

NGTB15N135IHRWG

IGBT with Monolithic Free Wheeling Diode

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop (FS) Trench construction, and provides superior performance in demanding switching applications, offering both low on-state voltage and minimal switching loss. The IGBT is well suited for resonant or soft switching applications.

Features

- Extremely Efficient Trench with Fieldstop Technology
- 1350 V Breakdown Voltage
- Optimized for Low Case Temperature in IH Cooker Application
- Reliable and Cost Effective Single Die Solution
- These are Pb-Free Devices

Typical Applications

- Inductive Heating
- Consumer Appliances
- Soft Switching

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-emitter voltage	V_{CES}	1350	V
Collector current @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	I_C	30 15	A
Pulsed collector current, T_{pulse} limited by $T_{J\text{max}}$	I_{CM}	60	A
Diode forward current @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	I_F	30 15	A
Diode pulsed current, T_{pulse} limited by $T_{J\text{max}}$	I_{FM}	60	A
Gate-emitter voltage Transient Gate-emitter Voltage ($T_{\text{pulse}} = 5 \mu\text{s}$, $D < 0.10$)	V_{GE}	± 20 ± 25	V
Power Dissipation @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	P_D	357 178	W
Operating junction temperature range	T_J	-40 to +175	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to +175	$^\circ\text{C}$
Lead temperature for soldering, 1/8" from case for 5 seconds	T_{SLD}	260	$^\circ\text{C}$

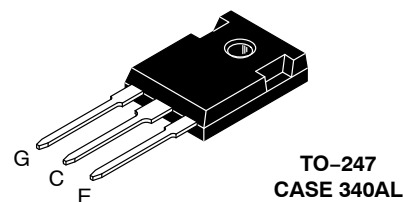
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ON Semiconductor®

<http://onsemi.com>

15 A, 1350 V
 $V_{CEsat} = 2.15 \text{ V}$
 $E_{off} = 0.42 \text{ mJ}$



MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
NGTB15N135IHRWG	TO-247 (Pb-Free)	30 Units / Rail

NGTB15N135IHRWG

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction-to-case	$R_{\theta JC}$	0.42	$^{\circ}\text{C}/\text{W}$
Thermal resistance junction-to-ambient	$R_{\theta JA}$	40	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
-----------	-----------------	--------	-----	-----	-----	------

STATIC CHARACTERISTIC

Collector-emitter breakdown voltage, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, I_C = 500\ \mu\text{A}$	$V_{(BR)CES}$	1350	-	-	V
Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 15\text{ A}$ $V_{GE} = 15\text{ V}, I_C = 15\text{ A}, T_J = 175^{\circ}\text{C}$	V_{CEsat}	-	2.15 2.25	2.65 -	V
Gate-emitter threshold voltage	$V_{GE} = V_{CE}, I_C = 250\ \mu\text{A}$	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector-emitter cut-off current, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, V_{CE} = 1350\text{ V}$	I_{CES}	-	-	0.1	mA
Gate leakage current, collector-emitter short-circuited	$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	I_{GES}	-	-	100	nA

DYNAMIC CHARACTERISTIC

Input capacitance	$V_{CE} = 20\text{ V}, V_{GE} = 0\text{ V}, f = 10\text{ kHz}$	C_{ies}	-	3560	-	pF
Output capacitance		C_{oes}	-	87	-	
Reverse transfer capacitance		C_{res}	-	68	-	
Gate charge total	$V_{CE} = 600\text{ V}, I_C = 15\text{ A}, V_{GE} = 15\text{ V}$	Q_g	-	156	-	nC
Gate to emitter charge		Q_{ge}	-	27	-	
Gate to collector charge		Q_{gc}	-	70	-	

SWITCHING CHARACTERISTIC, INDUCTIVE LOAD

Turn-off delay time	$T_J = 25^{\circ}\text{C}$ $V_{CC} = 600\text{ V}, I_C = 15\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$	$t_{d(off)}$	-	170	-	ns
Fall time		t_f	-	200	-	
Turn-off switching loss		E_{off}	-	0.42	-	
Turn-off delay time	$T_J = 150^{\circ}\text{C}$ $V_{CC} = 600\text{ V}, I_C = 15\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$	$t_{d(off)}$	-	190	-	ns
Fall time		t_f	-	290	-	
Turn-off switching loss		E_{off}	-	0.95	-	

DIODE CHARACTERISTIC

Forward voltage	$V_{GE} = 0\text{ V}, I_F = 15\text{ A}, T_J = 25^{\circ}\text{C}$ $V_{GE} = 0\text{ V}, I_F = 15\text{ A}, T_J = 175^{\circ}\text{C}$	V_F	-	1.85 2.75	2.10 -	V
-----------------	---	-------	---	--------------	-----------	---

NGTB15N135IHRWG

TYPICAL CHARACTERISTICS

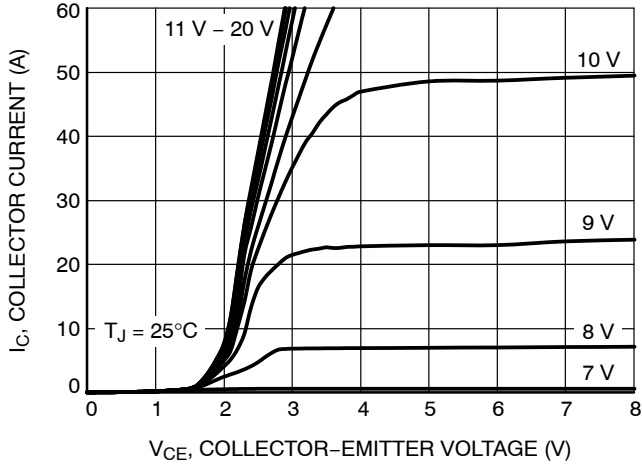


Figure 1. Output Characteristics

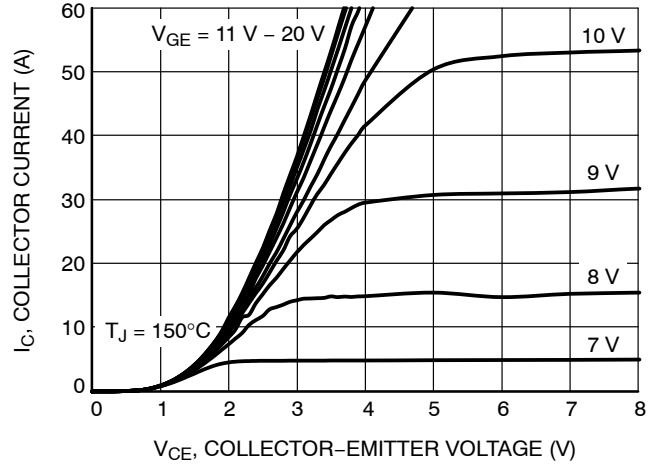


Figure 2. Output Characteristics

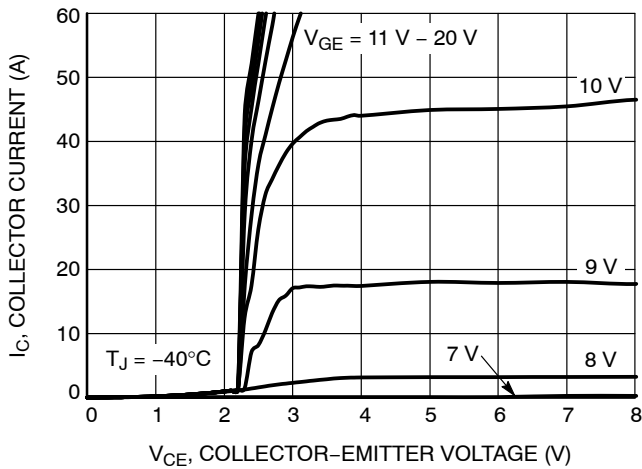


Figure 3. Output Characteristics

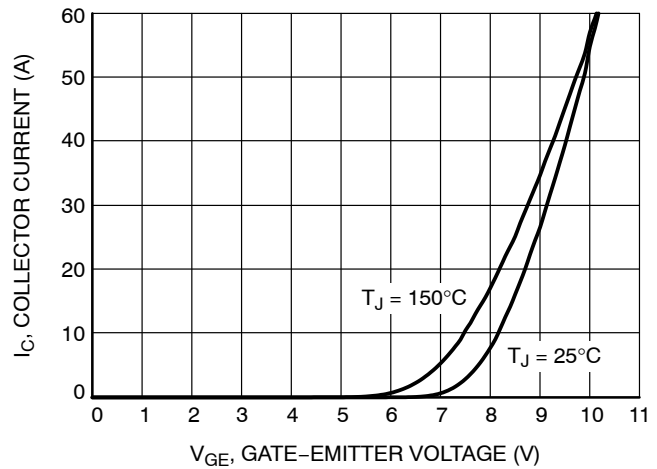


Figure 4. Typical Transfer Characteristics

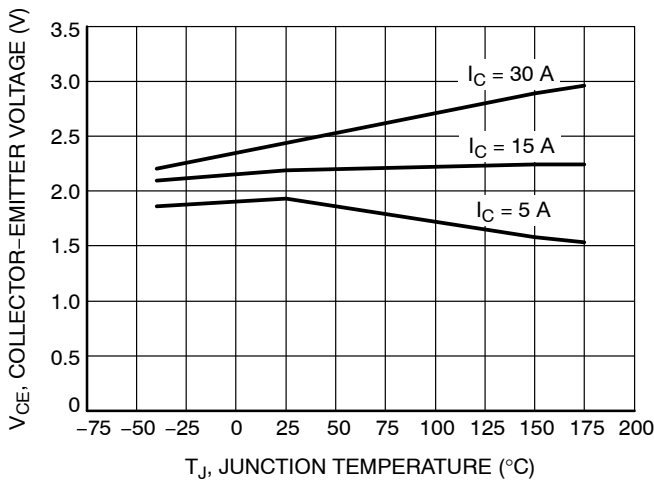


Figure 5. $V_{CE(sat)}$ vs. T_J

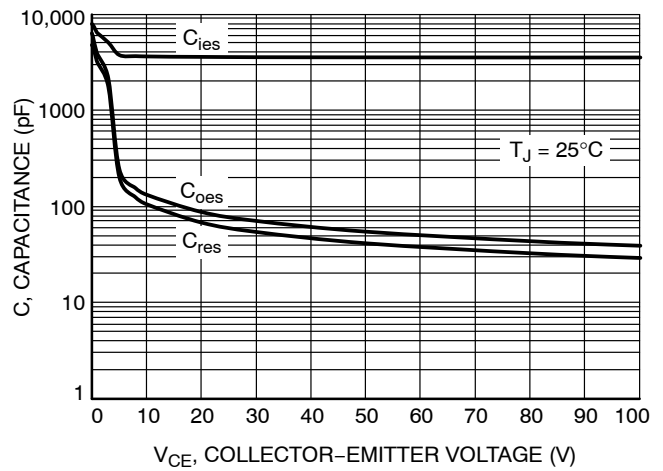


Figure 6. Typical Capacitance

NGTB15N135IHRWG

TYPICAL CHARACTERISTICS

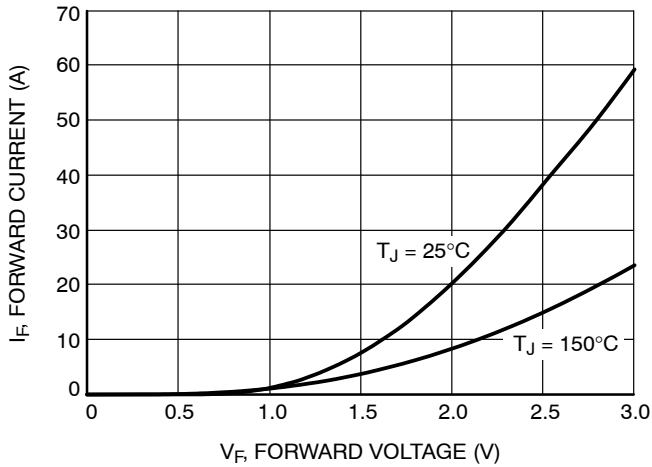


Figure 7. Diode Forward Characteristics

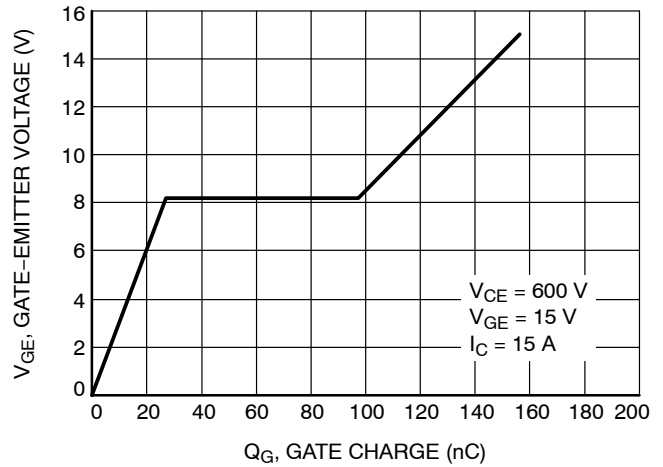


Figure 8. Typical Gate Charge

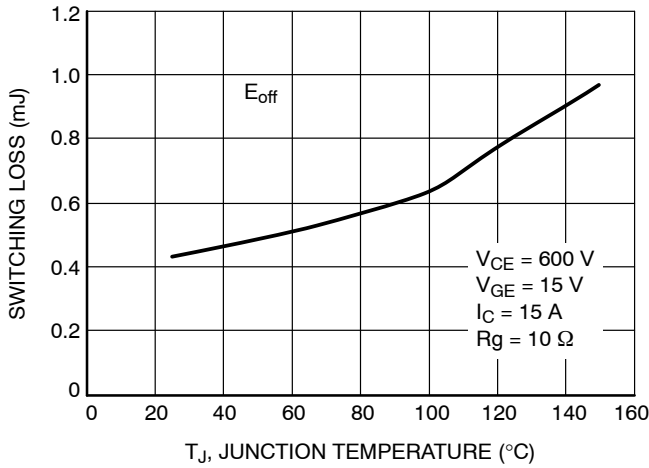


Figure 9. Switching Loss vs. Temperature

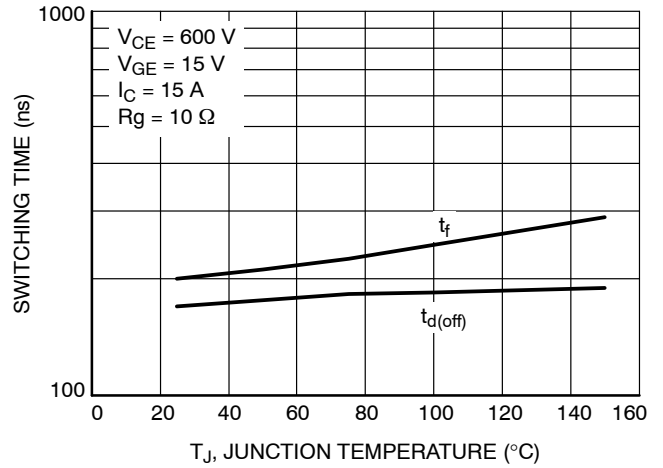


Figure 10. Switching Time vs. Temperature

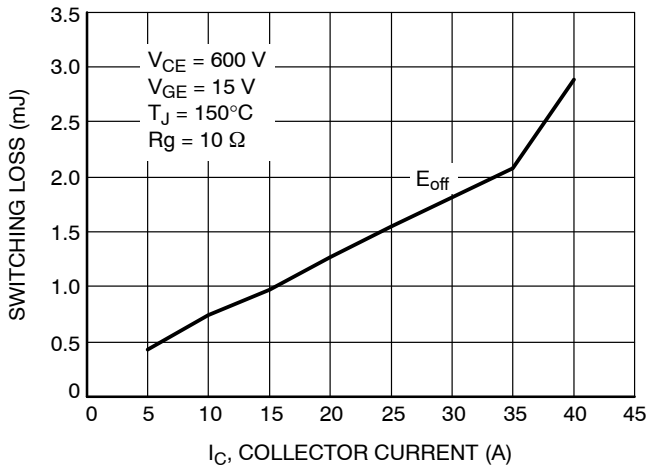


Figure 11. Switching Loss vs. I_C

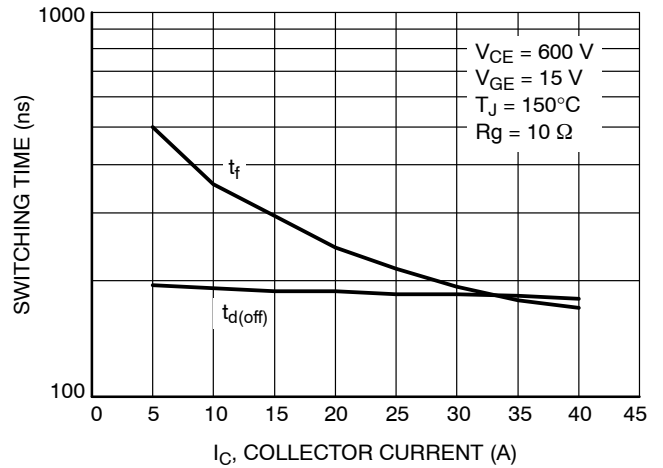


Figure 12. Switching Time vs. I_C

NGTB15N135IHRWG

TYPICAL CHARACTERISTICS

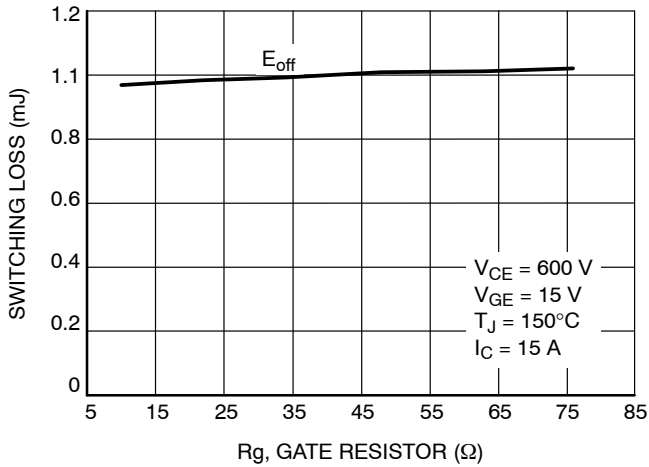


Figure 13. Switching Loss vs. Rg

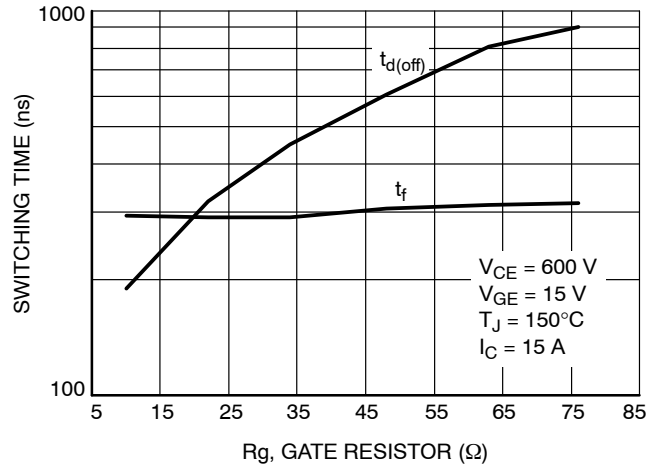


Figure 14. Switching Time vs. Rg

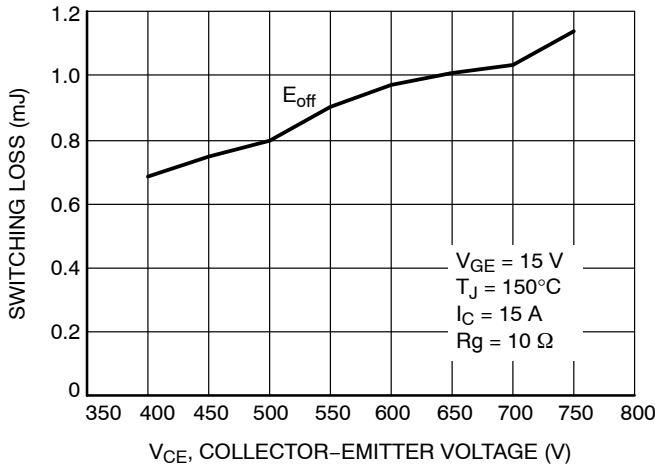


Figure 15. Switching Loss vs. V_{CE}

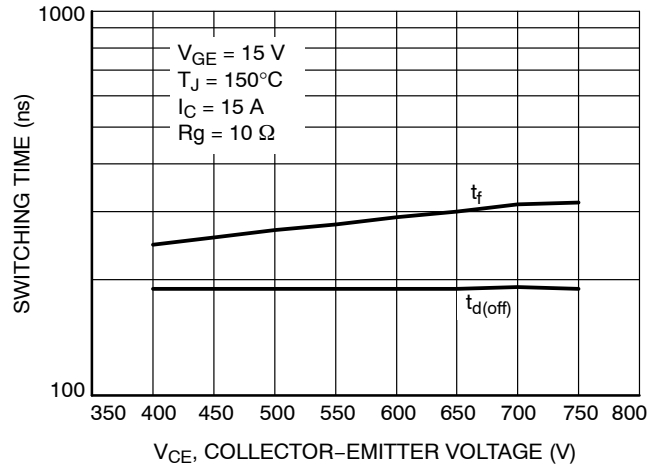


Figure 16. Switching Time vs. V_{CE}

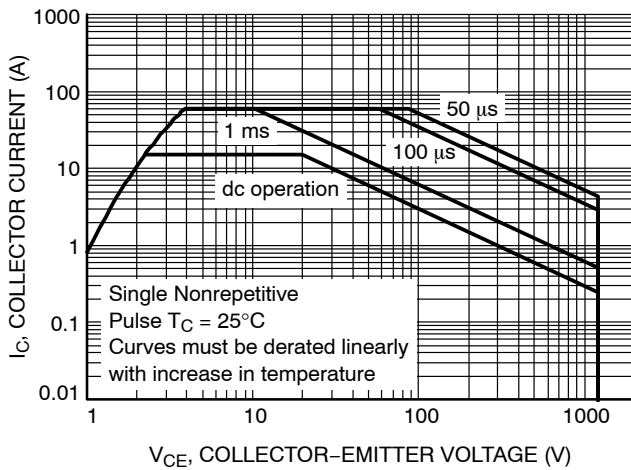


Figure 17. Safe Operating Area

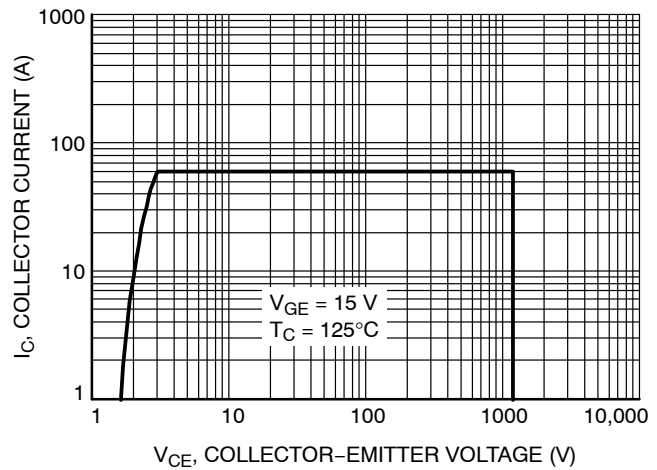


Figure 18. I_C vs. V_{CE}

NGTB15N135IHRWG

TYPICAL CHARACTERISTICS

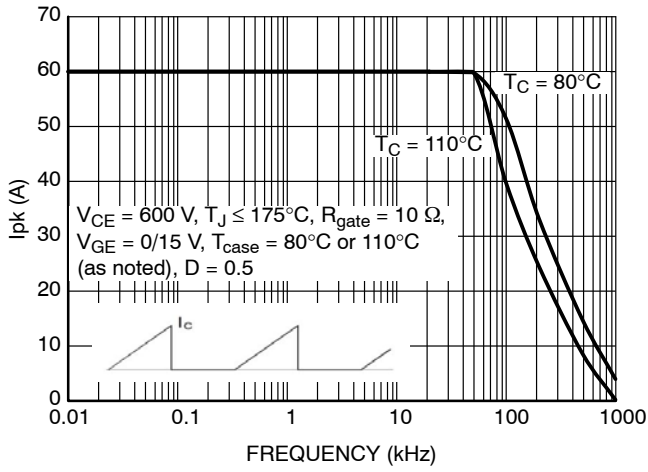


Figure 19. Collector Current vs. Switching Frequency

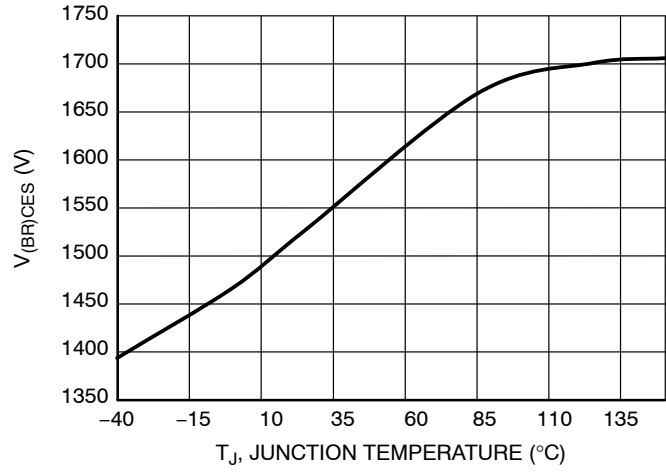


Figure 20. Typical $V_{(BR)CES}$ vs. Temperature

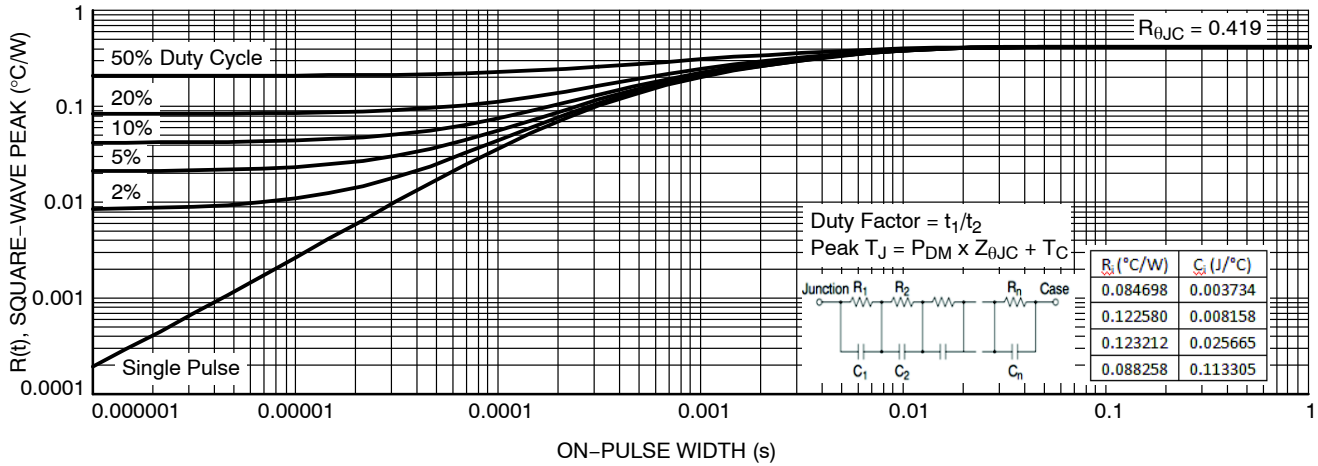


Figure 21. IGBT Transient Thermal Impedance

NGTB15N135IHRWG



Figure 22. Test Circuit for Switching Characteristics

NGTB15N135IHRWG



Figure 23. Definition of Turn On Waveform



Figure 24. Definition of Turn Off Waveform

